

# Soft X-Ray ARPES at Swiss Light Source: From Bulk Materials to Buried Heterostructures and Impurities

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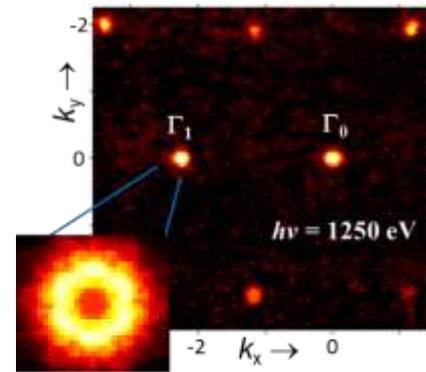
Soft-X-ray ARPES, operating in the energy range around 1 keV, benefits from enhanced photoelectron escape depth, concomitant sharp resolution in 3D electron momentum  $\mathbf{k}$ , and resonant photoexcitation delivering elemental and chemical-state specificity. High energy resolving power ( $>30000$ ) and photon flux ( $>10^{13}$  ph/s/0.01%BW) delivered by the ADRESS beamline of Swiss Light Source allow expansion of this novel experimental technique from bulk materials to buried heterostructures and impurities [1] which are in the heart of electronic and spintronic devices.

*Bulk materials.* – Applications to 3D electronic structure of bulk materials are illustrated by the layered chalcogenide  $VSe_2$  where we discover 3D-nesting of its Fermi surface stabilizing exotic charge density waves [2]. Other examples include lattice-distortion effects in manganates connected with their magnetoresistance [3], 3D topological states in Weil semimetals, etc.

*Buried heterostructures.* – Semiconductor systems are illustrated by AlGaIn/GaN high-electron-mobility transistor heterostructures, where soft-X-ray ARPES finds anisotropic band structure and Fermi surface (figure) of the interfacial quantum-well states, resulting in anisotropic non-linear electron transport [4]. For the "drosophila" oxide interface  $LaAlO_3/SrTiO_3$ , resonant photoexcitation of the Ti-derived interfacial charge carriers resolves their multiphonon polaronic nature, fundamentally limiting their mobility [5]. Further cases include EuO/Si spin injectors, EuS/ $Bi_2Se_3$  topological interfaces, etc.

*Impurity systems.* – Applications to diluted magnetic semiconductors are illustrated by Ga(Mn)As, where resonant photoexcitation of Mn-derived impurity states identifies their energy alignment and hybridization with the host GaAs states, elucidating the nature of the ferromagnetic electron transport [6]. Other cases include magnetic V impurities in the topological  $Bi_2Se_3$  competing with the quantum anomalous-Hall effect, etc.

Further prospects of soft-X-ray ARPES are connected with the multichannel spin detector iMott [7]. Boosting the detection efficiency by few orders of magnitude, this detector will deliver previously unthinkable information about  $\mathbf{k}$ -resolved spin texture of buried heterostructures and impurities. Furthermore, in 2023 the Swiss Light Source will be upgraded to the diffraction-limited source based on multibend achromats, promising an increase of the coherent fraction and reduction of the horizontal emittance by a factor of  $>30$ . The ADRESS beamline will receive an Apple-Knot undulator to reduce on-axis thermal load by two orders of magnitude. This source and optical elements with ultra-low slope errors of  $\sim 0.1 \mu\text{rad}$  will push the beamline resolving power above 100'000, allowing access to electronic structure and electron-boson interactions on the few-meV energy scale.



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[2] V.N. Strocov et al., *Phys. Rev. Lett.* **109** (2012) 086401

[3\*] L.L. Lev et al., *Phys. Rev. Lett.* **114** (2015) 237601

[4\*] L.L. Lev et al., *Nature Comm.* **9** (2018) 2653

[5] C. Cancellieri et al., *Nature Comm.* **7** (2016) 10386

[6] M. Kobayashi et al., *Phys. Rev. B* **89** (2014) 205204

[7] V.N. Strocov et al., *J. Synchr. Rad.* **22** (2015) 708

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